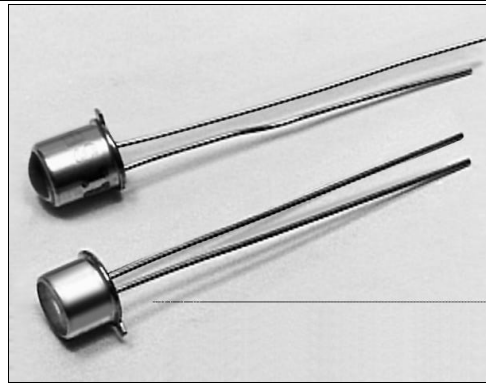


SE3470/5470

AlGaAs Infrared Emitting Diode

FEATURES

- TO-46 metal can package
- Choice of flat window or lensed package
- 90° or 20° (nominal) beam angle option
- 880 nm wavelength
- Higher output power than GaAs at equivalent drive currents
- Wide operating temperature range (-55°C to +125°C)
- Ideal for high pulsed current applications
- Mechanically and spectrally matched to SD3421/5421 photodiode, SD3443/5443/5491 phototransistor, SD3410/5410 photodarlington and SD5600 series Schmitt trigger



INFRA-83.TIF

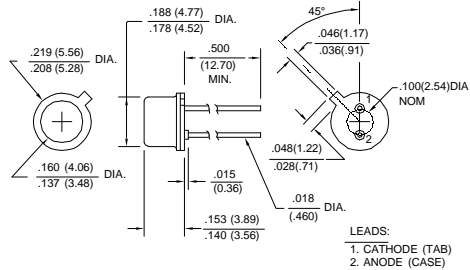
DESCRIPTION

The SE3470/5470 series consists of aluminum gallium arsenide infrared emitting diode mounted in a TO-46 metal can package. The SE3470 series has flat window cans providing a wide beam angle, while the SE5470 series has glass lensed cans providing a narrow beam angle. These devices typically exhibit 70% greater power output than gallium arsenide devices at the same forward current. The TO-46 packages offer high power dissipation capability and are ideally suited for operation in hostile environments.

OUTLINE DIMENSIONS in inches (mm)

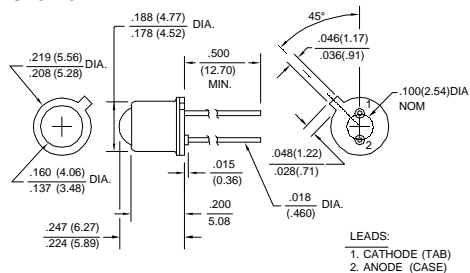
Tolerance	3 plc decimals	±0.005(0.12)
	2 plc decimals	±0.020(0.51)

SE3470



DIM_005a.ds4

SE5470



DIM_005b.ds4

Honeywell

Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

